Complex formation of ethylenedioxyethylenedithiotetrathiafulvalene (EDOEDT-TTF: EOET) and its self-assembling ability

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36 kinds of donor(D)-acceptor(A) type charge transfer (CT) solids were prepared based on ethylenedioxyethylenedithiotetrathiafulvalene (EDOEDT-TTF or EOET), which is a hybrid molecule of bis(ethylenedioxy)-TTF (BEDO-TTF or BO) and bis(ethylenedithio)-TTF (BEDT-TTF or ET). A plot of the first CT absorption bands in solids against the difference in first redox potential between donor and acceptor molecules (ΔE) classified the complexes into five groups, A: highly conductive CT complexes with partial CT state and segregated stacks, B: partially ionic CT insulators with alternating stacks, C: essentially neutral clathrate complexes, **D**: neutral CT insulators with alternating stacks, and **E**: completely ionic insulators. Group A is spread out over an extensive ΔE range compared to one-dimensional organic metals such as the 1 : 1 TTF-TCNQ system. This indicates that the EOET complexes among this group have a high electronic dimensionality arising from the self-aggregation of the EOET molecules in a fashion similar to the BO ones. However, the self-assembling ability of the EOET molecules is less pronounced than that of the BO ones, thereby giving a metal-insulator transition for many complexes among Group A. The reduced self-assembling ability also affords alternating stacks in (MeO)₂TCNQ, BTDA-TCNQ (Group B) and *p*-iodanil (Group C) complexes. Two structurally distinct complexes were prepared with spherical C_{60} (Group **D**), one containing concave EOET molecules and one-dimensional C_{60} columns, and the other planar EOET and two-dimensional C_{60} layers. The F₄TCNQ complex (Group E) exhibits an antiferromagnetic ordering below 7 K, which is intermediate between those in (BO)(F₄TCNQ) (5.4 K) and (ET)(F₄TCNQ) (14 K).

1 Introduction

Conducting charge transfer (CT) compounds based on bis(ethylenedithio)tetrathiafulvalene (BEDT-TTF or ET) or bis(ethylenedioxy)-TTF (BEDO-TTF or BO) (the main compounds in this paper are presented in Chart 1) have so far offered a number of fascinating materials and phenomena that give rise to new concepts in the field of materials science.¹ For example, (1) *d*-wave type superconductivity claimed for some ET superconductors,² (2) a new technique applied on many two-dimensional ET metals to investigate the Fermi-surface topology (*i.e.*, angular dependent magnetoresistance oscillation),³ (3) a metallic mono- or multilayer fabricated at the air–water interface using BO compounds,⁴ (4) metallic and transparent polycarbonate composite films prepared by halogen doped BO.⁵

These fascinating materials and phenomena are largely attributed to the intermolecular interactions between the particular donor molecules (ET or BO), which essentially depend on the characteristics of the component molecules. Hereinafter, intermolecular interactions in connection with the crystal and electronic structures of ET and BO will be separately reviewed.

ET molecules have afforded more than 50 superconductors and a wide variety of one- to two-dimensional metallic and semiconducting compounds.⁶ In the solids the ET molecules pile up with sliding overlap in order to minimize the steric hindrance by the terminal ethylene groups which have great conformational freedom. This results in weakened face-to-face π -intermolecular interactions. On the other hand, the molecule has a strong tendency to form a variety of intermolecular sulfur-to-sulfur $(S \cdots S)$ atomic contacts along the side-by-side direction. Thus the two-dimensional crystal and electronic structures are established as a compromise of these two kinds of medium intermolecular interactions. Moreover, there are a variety of donor-anion and anion-anion intermolecular interactions in the ET compounds in addition to the donordonor ones, thereby giving numerous molecular packing patterns of the ET molecules and hence the presence of polymorphism, complex isomerism, clathrate character or various molecular compositions in the compounds.

The BO molecules have afforded a number of twodimensional metals including two superconductors.⁷ Many BO compounds exhibit metallic behavior down to low temperatures even in severely disordered systems such as compressed pellets, Langmuir–Blodgett (LB) films and composite

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Chart 1 Chemical structures of donor and acceptor molecules in the text.

polymer films,^{4,5,7} while the ET compounds in such sample forms are prevented from showing metallic behavior at low temperatures. The exceptional stability of the metallic state in the BO compounds is attributed to the strong donor-donor interactions (self-assembling ability) of BO molecules, which are established by the combination of the short intermolecular CH…O atomic contacts along the stacking direction and the robust $S_{in} \cdots S_{in}$ (S_{in}: sulfur atom in the TTF skeleton) atomic contacts along the side-by-side direction. As a result, the BO molecules crystallize with a limited number of packing patterns giving the structurally and electronically two-dimensional structures. Owing to the negligible or otherwise rather small transfer interactions along the stacking axis, the two-dimensional nature is accomplished by the multiple transfer interactions oblique to the stacking axis. The bandwidth of the HOMO band $(0.9-1.2 \text{ eV})^{7a}$ is slightly more than that of θ -type ET compounds $(0.8-0.9 \text{ eV})^8$ and the notable stability of the metallic state prevents the occurrence of the superconducting state.

Thus it is of interest to investigate the characteristics of the hybrid molecule of BO and ET—*i.e.* ethylenedioxyethylenedithio-TTF (EDOEDT-TTF or EOET). This molecule is anticipated to exhibit a reduced self-assembling ability in the compounds and a decreased bandwidth compared to those in the BO compounds. Moreover, the decrease in molecular symmetry would facilitate the localization of itinerant electrons due to the existence of disorder and/or non-periodicity in solids. Keeping in mind these expected features, we report here mainly the structural properties of the EOET complexes with organic acceptor molecules to demonstrate the structural diversity. A preliminary study has been previously reported.⁹

EOET was first synthesized by Kini *et al.* in 1990.¹⁰ They argued that the electrochemical property of the EOET molecule is influenced by both parent molecules BO and ET, *i.e.*, the first redox potential $(E^{1}_{1/2}(D))$ of the molecule is

midway between those of the parent molecules. However, experimental work on EOET complexes remains sparse because of the difficulty in attaining the solids. At present, only the following reports have appeared, (1) structural works on EOET itself, ¹⁰ C₆₀ complex, ¹¹ and AuI₂ (τ - and β -phases)¹² and Hg₃Br₈¹³ salts, (2) conducting works on a complex with behenic acid, ¹⁴ and AuI₂ (τ - and β -phases), ¹² Cu(NCS)₂, ^{12,15} Pt(CN)₄, ¹⁶ and Pd(CN)₄¹⁶ salts, as well as (3) preparation of I₃ and IBr₂ salts, ¹⁷ and 7,7,8,8-tetracyano-*p*-quinodimethane (TCNQ) complex.^{17,18}

2 Results and discussion

2.1 Electron-donating strength

The electron-donating strength of the EOET molecule is evaluated on the basis of the $E^{1}_{1/2}(D)$ value and the CT transition energy of the *sym*-trinitrobenzene (TNB) complex in solution (hv_{CT}^{soln}). Both the $E^{1}_{1/2}(D)$ (+0.47 V vs. saturated calomel electrode (SCE)) and the hv_{CT}^{soln} values (15.5 × 10^{3} cm⁻¹ in CHCl₃) are midway between those of parents, BO ($E^{1}_{1/2}(D) = +0.43$ V, $hv_{CT}^{soln} = 15.0 \times 10^{3}$ cm⁻¹) and ET ($E^{1}_{1/2}(D) = +0.53$ V, $hv_{CT}^{soln} = 16.1 \times 10^{3}$ cm⁻¹), indicating that the electron-donating ability of EOET is also midway between those of BO and ET as reported previously.^{10,18} The difference between the second and first redox potentials (0.26 V) is closely similar to those of BO (0.26 V) and ET (0.25 V), implying a comparable bare on-site Coulomb repulsive energy (U_0) between them.

2.2 Classification of charge transfer complex

Table 1 summarizes the results of the complex formation: acceptor molecules with their first redox potential $(E_{1/2}^{l}(A) vs.$ SCE), the difference in first redox potentials between EOET and each acceptor molecule ($\Delta E = E_{1/2}^{l}(D) - E_{1/2}^{l}(A)$),

Table 1 Appearance, stoichiometry, optical and conductivity data of EOET complexes together with redox potentials $(E_{1/2}^{1}(A))$ and ΔE $E^{1}_{1/2}(\text{EOET}) - E^{1}_{1/2}(\text{A}))$

No.	Acceptor ^a	$E^{1}_{1/2}(A)^{b}/V$	$\Delta E^{c}/V$	Appearance ^d	$D : A : (solv)^e$	$hv_{\rm CT}^{\rm solidf}/10^3 {\rm ~cm}^{-1}$	$\sigma_{\rm RT}/{\rm S~cm^{-1}}$ [$\epsilon_{\rm a}/{\rm meV}$], $T_{\rm MI}^{\ g}$
1a	HCBD	0.72	-0.25	Dark green pwd		3.4	12(P), $T_{\rm MI} = 120 \ {\rm K}$
1b	HCBD	0.72	-0.25	Black blue pwd	1:1	11.3	< 10 ⁻⁸
2	F ₄ TCNQ	0.60	-0.13	Black needle	1:1	6.7	1.8×10^{-6} (P) [160]
3	DDQ	0.56	-0.10	Brown pwd	$7:8:2(H_2O)$	3.4	6.7×10^{-1} (P) [16]
4	DIDQ	0.51	-0.04	Brown pwd	$2 : 1 : 0.5(H_2O)$	3.6	3.6(P) [25]
5	CF ₃ TCNQ	0.44	0.03	Green pwd	2:1	3.2	$5.8(P), T_{MI} = 250 \text{ K}$
6	F ₂ TCNQ	0.41	0.06	Green polycry	$2 : 1 : 1(H_2O)$	3.5	$35(P), T_{MI} = 15 K$
7	DCNNQ	0.38	0.09	Black pwd	$7:4:4(H_2O)$	4.0	2.3×10^{-1} (P) [76]
8	$Q(CN)_2$	0.35	0.11	Brown pwd	_	5.9	<10 ⁻⁸
9	FTCNQ	0.32	0.15	Black polycry	1:1	3.4	7.7(P), $T_{\rm MI} = 100 {\rm K}$
10	DTENF	0.23	0.24	Dark green pwd	2:1:1(AN)	3.2	8.3×10^{-1} (P) [120]
11	TCNQ	0.22	0.25	Black plate	1:1	3.3	7.7, $T_{\rm MI} = 165 - 100 {\rm K}$
12	DCNQ	0.21	0.26	Brown pwd	2:1	3.8	3.5(P) [30]
13	MeTCNQ	0.19	0.28	Black polycry	4:3	3.3	$1.3(P) T_{MI} = 100 \text{ K}$
14	Et ₂ TCNQ	0.15	0.32	Green pwd	2:1	2.9	$15(P) T_{MI} = 120 \text{ K}$
15	Me ₂ TCNQ	0.15	0.32	Black pwd	1:1	6.0	<10 ⁻⁸
16	(MeO) ₂ TCNQ	0.05	0.42	Black plate	2:1	6.4	$< 10^{-8}$
17	QCl ₄	0.05	0.42	Brown pwd	$8 : 9 : 1(H_2O)$	4.0	2.9(P), $T_{\rm MI} = 200 \text{ K}$
18a	QF₄	0.04	0.43	Dark brown pwd	_	4.8	3.1×10^{-3} (P) [130]
18b	QF ₄	0.04	0.43	Black pwd	_	11.8	<10 ⁻⁸
19	QBr ₄	0.04	0.43	Black polycry	3:2	11.1	$< 10^{-8}$
20a	BTDA-TCNQ	0.03	0.44	Black pwd	3:2	2.1	23(P), $T_{\rm MI} = 200 {\rm K}$
20b	BTDA-TCNO	0.03	0.44	Black needle	1:1	7.6	<10 ⁻⁸
20c	BTDA-TCNO	0.03	0.44	Black plate	1:2	7.0	$< 10^{-8}$
21	DTNF	0.02	0.45	Green pwd	1:1	8.2	3.2×10^{-9} [420]
22	(EtO) ₂ TCNQ	0.01	0.46	Dark brown pwd	2:1	8.1	<10 ⁻⁸
23	QI ₄	-0.02	0.49	Black plate	2:1	9.9	$< 10^{-8}$
24a	OBr ₂ (OH) ₂	-0.12	0.59	Black polycry	_	3.4	14, $T_{\rm MI} = 260 \ {\rm K}$
24b	QBr ₂ (OH) ₂	-0.12	0.59	Black pwd	_	10.7	<10 ⁻⁸
25	QCl ₂ (OH) ₂	-0.13	0.60	Light brown pwd	_	3.3	1.8(P) [24]
26	TENF	-0.14	0.61	Black pwd	_	11.1	< 10 ⁻⁸
27	TNF	-0.43	0.89	Black block	4:3	10.7	$< 10^{-8}$
28a	C ₆₀	-0.44	0.90	Black block	1 : 1 : 1(Bz)	11.8	$< 10^{-8}$
28b	C ₆₀	-0.44	0.90	Black plate	1 : 1 : 1(Bz)	11.8	$< 10^{-8}$
29	H ₂ TNBP	-0.56	1.03	Black polycry	_ ``	12.0	$< 10^{-8}$
30	DNBP	-0.98	1.45	Black plate	6:5	14.8	$< 10^{-8}$
a				1			4

^aSee Chart 1. ^bFirst redox potential of acceptor vs. SCE. ^cDifference in first redox potential between donor and acceptor. ^dpwd: powder, polycry: polycrystals. "By elemental or structural analysis, AN: acetonitrile, Bz: benzene, --: not known. "First CT absorption band in KBr pellet. ^gT_{MI}: metal-insulator transition temperature, P: pellet sample.

appearance, stoichiometry, the first CT absorption band in KBr pellet (hv_{CT}^{solid}), and the conductivity at RT (σ_{RT}) together with the activation energy (ε_a) or temperature at which metal-insulator (MI) transition occurs $(T_{\rm MI})$. Fig. 1 plots the $hv_{\rm CT}^{\rm solid}$ values against the ΔE ones for the

EOET complexes obtained. The numbering for the complexes



Fig. 1 A plot of the first transition energy in solid (hv_{CT}^{solid}) against the difference in redox potential between EOET and acceptor molecules (ΔE) . For the V-shaped line, and the vertical and horizontal dotted lines, see text. Numbers correspond to those in the first column of Table 1. \bullet : Group A, \bigcirc : Group B, \blacksquare : Group C, \square : Group D, \blacktriangle : Group E.

follows the order of electron-accepting ability of the acceptor molecules. The right- and left-hand sides of the V-shaped line represent the theoretical CT transition energies for neutral (hv_{CT}^{N}) and ionic (hv_{CT}^{I}) CT solids with D–A alternating stacks, respectively,¹⁹ whereas the low-lying bands below 5 × 10^3 cm⁻¹ (horizontal dashed line) are generally attributed to an intermolecular transition between the same component species with partially ionic ground state, 7a,20,21 which is required for the conducting materials. Based on these assignments, the EOET complexes could be classified into the following five categories (Groups A-E). Interestingly, some particular combinations of component molecules provide multiple phases concerning the stoichiometry, structure, and/or conductivity (1a-1b, 18a-18b, 20a-20c, 24a-24b, 28a-28b), and these complexes except 1 and 28 locate in the vicinity of the right vertical line (vide infra) as shown in Fig. 1. Such phenomena, *i.e.* polymorphism, complex isomerization, monotropic neutral–ionic isomers, and so forth,^{22,23} have also been reported for the BEDO-DBTTF,²⁰ ET,²⁴ TSF²⁵ and TMTSF²⁶ systems but rarely for the BO system.

Group A. 17 highly conductive complexes (1a, 3-7, 9-14, 17, 18a, 20a, 24a, 25) with the low-lying CT band below 5 \times 10^3 cm⁻¹, are obtained in the following redox region:

$$-0.25 \leqslant \Delta E \leqslant 0.60 \text{ V} \tag{1}$$

This range is much wider compared to that of the 1 : 1 TTF-TCNQ system, as represented by the two vertical dotted lines in Fig. 1 or eqn. (2).

$$-0.02 \leqslant \Delta E \leqslant 0.34 \text{ V} \tag{2}$$

The extension of the lower limit in ΔE is apparently owing to the formation of non 1 : 1 stoichiometry (3, 4), in which the excess component would be in a partially ionized state. On the other hand, the extension of the upper limit is indicative of a higher electronic dimensionality than that of the TTF–TCNQ system, as demonstrated in the BO compounds.^{7a,27} As far as the plot of hv_{CT}^{solid} against ΔE is concerned, the highly conductive region in the EOET system is almost identical to that in the BO system,^{7a} indicating the existence of the strong self-assembling ability of the EOET molecules.

Indeed, the temperature dependence of resistivity of the complexes in this group is metallic, although they exhibit a MI transition. The presence of the MI transition in many EOET complexes indicates a weaker self-assembling ability compared to that of the BO compounds in which such a transition has been rarely found.

The F₂TCNQ complex (6) clearly exhibits a metallic temperature dependence even in the compressed pellet form down to 15 K, below which the resistivity increases gradually (Fig. 2). A plot of $\ln\rho$ against $T^{-1/4}$ below 12 K gives an excellent straight line, as expected for the three-dimensional variable-range hopping system.²⁸

The resistivity of other complexes showing the MI transition (see Table 1) is rather temperature independent down to $T_{\rm MI}$ as demonstrated in Fig. 2 for **1a**, **11** and **17**. Particularly it should be noted that the resistivity of the TCNQ complex (**11**) remains invariant down to *ca*. 120 K ($\sigma_{\rm RT} = 7.7$ S cm⁻¹), where it then begins to increase more rapidly. Thus the metallic state of **11** is thermodynamically more stable relative to those of semiconductive (BO)(TCNQ)^{7a} and triclinic (ET)(TCNQ) with a MI transition at 330 K.^{24b} The ε_a value of **11** below 100 K is evaluated to 22 meV, which is much smaller than those of (BO)(TCNQ) and (ET)(TCNQ) (40–70 meV).

Fig. 3a shows uniform segregated columns composed of individual component molecules in 11 (for crystallographic data of 11 and other complexes, see Table 2).¶ The TCNQ molecules form a bond-over-ring overlap mode with an interplanar spacing of 3.34 Å. The overlap integral t1 (13.3 \times 10⁻³) is more than 100 times those of other directions, indicating the one-dimensional electronic structure of the TCNQ part. The EOET molecules stack in a head-to-head manner with an interplanar spacing of 3.66–3.67 Å as seen in Fig. 3b. Such a stacking manner as to give short CH…O hydrogen bonds (dashed lines in Fig. 3a, 3.55 and 3.56 Å vs. van der Waals (vdW) distance of CH…O 3.72 Å²⁹) is necessary for EOET molecules to self-assemble along the face-to-face direction. It is thus evident that the self-aggregation of the EOET molecules is exerted by the hydrogen bonds along the stack like that of the BO molecules.⁷ A slip from each other along the molecular short axis (Fig. 3b) also resembles closely the BO compounds.74

Each segregated EOET column also slips from the neighboring column along the molecular long axis, and no pronounced short S…S atomic contact is observed along the side-by-side direction contrary to many BO and ET compounds. The side-by-side S…S distances are 3.67 Å for S_{in} … S_{in} and 3.72 and 3.81 Å for S_{in} … S_{out} . These values are slightly larger than the corresponding vdW distance (3.60 Å) due to the lower symmetry of EOET molecule and the relative orientation of EOET columns. Fig. 4 schematically demonstrates the typical S…S atomic contacts along the side-by-side direction in (a) BO, (b) EOET and (c) ET compounds where the molecular



Fig. 2 Temperature dependence of resistivity on the compressed pellets for F_2TCNQ (6, the magnitude is multiplied by 10²), HCBD (1a, ×10) and *p*-QCl₄ (17, ×1), and on single crystal for TCNQ (11, ×10⁻²) complexes among Group A.

shapes are exaggerated for easy understanding. Since the HOMO coefficient of inner chalcogen atoms of BO, ET or EOET is generally 3-4 times greater than that of the outer chalcogen ones, the transfer interactions generated by $S_{\mathrm{in}} {}^{\mathrm{\cdots}} S_{\mathrm{in}}$ contacts along the side-by-side direction are significantly important compared to those by $S_{in}{\cdots}X_{out}$ and $X_{out}{\cdots}X_{out}$ contacts.^{6a} For the BO compounds, the size difference between oxygen and sulfur atoms enables the formation of robust sideby-side $S_{in} \cdots S_{in}$ contacts, giving rise to a few particular patterns of $X \cdots X$ contacts (Fig. 4a). On the other hand, the $S_{in} \cdots S_{in}$ contacts are not so attainable in the usual ET compounds due to the steric hindrance exerted by bulky sixmembered rings (for κ -phase, see Fig. 4c). Hence no particular $S_{in} \cdots S_{out}$ patterns are favorable and so various kinds of $S \cdots S$ contact are produced depending on the donor packing patterns $(\alpha, \beta, \theta, \kappa$ -phases, and so forth).^{6,30} For complex 11, the S^{...}S contacts are not as effective for obtaining the transverse transfer interactions relative to those in the BO and ET



Fig. 3 (a) Crystal structure of (EOET)(TCNQ) (11) viewed along the a^* -axis. Short CH…O atomic contacts are shown by dashed lines. *t*1 is the calculated overlap integral between TCNQ molecules (13.3×10^{-3}) and is 100 times more than those of other directions. (b) Overlap modes of EOET and TCNQ molecules in each segregated column.

[¶]Crystal data for (EOET)(TCNQ), (EOET)₂(*p*-iodanil), (EOET)₂-[(MeO)₂TCNQ], (EOET)(BTDA-TCNQ) and (EOET)(BTDA-TCNQ)₂ are available as supplementary data. CCDC reference numbers 175473–175477. See http://www.rsc.org/suppdata/jm/b1/b110605h/ for crystallographic files in .cif or other electronic format.

Table 2 Crystallographic data of EOET complexes with TCNQ (11), p-iodanil (23), (MeO)₂TCNQ (16) and BTDA-TCNQ (20b, 20c)^a

Complex	11	16	20b	20c	23
Acceptor (A)	TCNQ	(MeO) ₂ TCNQ	BTDA-TCNQ	BTDA-TCNQ	<i>p</i> -iodanil
EOET : À	1:1	2:1	1:1	1:2	2 : 1
Formula	$C_{22}H_{12}O_2N_4S_6$	C ₃₄ H ₂₄ O ₆ N ₄ S ₁₂	$C_{22}H_8O_2N_8S_8$	$C_{34}H_8O_2N_{16}S_{10}$	$C_{26}H_{16}O_6S_{12}I_4$
Formula weight	556.76	969.38	672.89	993.20	1316.82
Crystal system	Triclinic	Triclinic	Monoclinic	Triclinic	Triclinic
Space group	<i>P</i> 1	$P\bar{1}$	$P2_1/n$	<i>P</i> 1	$P\overline{1}$
aĺÅ	7.213(3)	9.887(4)	7.620(1)	7.541(1)	8.120(1)
b/Å	19.856(5)	12.024(4)	12.973(2)	9.169(1)	12.000(1)
c/Å	4.041(1)	9.387(4)	13.247(2)	15.216(2)	10.967(1)
α/°	92.08(1)	94.75(3)		93.948(7)	69.558(4)
β/°	89.61(2)	109.87(4)	91.316(8)	101.680(6)	108.343(4)
$\gamma /^{\circ}$	95.59(1)	103.17(7)		106.924(8)	104.786(4)
$V/Å^3$	575.6(3)	1006.2(7)	1309.2(3)	976.5(2)	937.7(1)
Z	1	1	2	1	1
$d_c/g \text{ cm}^{-3}$	1.61	1.60	1.71	1.69	2.33
μ/mm^{-1}	0.625	0.674	0.732	0.595	3.625
Diffractometer ^b	a	b	a	a	a
$2\theta_{\rm max}/^{\circ}$	55	50	55	55	50
No. of intensity measured	1822	4565	2517	3410	3576
Criterion for obsd reflections	$F_0 \geq 3\sigma(F_0)$	$F_0 \ge 4\sigma(F_0)$	$F_0 \geq 4\sigma(F_0)$	$F_0 \ge 2\sigma(F_0)$	$F_0 \ge 2\sigma(F_0)$
No. of refined parameters	304	256	193	540	217
R	0.057	0.055	0.070	0.068	0.033
^a Diffraction data were collected a	at room temperature. b	a: Mac Science DIP-202	20K, b: Mac Science M	IXC ^ĸ .	

compounds owing to both the low-symmetric molecular shape and the ordered molecular orientation (Fig. 4b), where the latter is necessary for EOET molecules to obtain the longitudinal transfer interactions effectively. This is indicative of the reduced self-assembling ability of the EOET molecules with respect to the BO ones, and thereby facilitates the occurrence of the MI transition as observed for many complexes among this group. More precise characterizations concerning the relation between crystal and electronic structures, physical properties and the mechanism of the MI transition will be described elsewhere.



Fig. 4 Schematic figures of S···S atomic contacts in typical (a) BO, (b) EOET and (c) ET compounds. Dotted lines indicate the comparatively short S···S atomic contacts. Thick dotted lines: S_{in} ···S_{in}, medium one: S_{in} ···S_{out} and thin dotted lines: S_{out} ···S_{out}. Examples are (BO)₅(HCTMM)(PhCN)₂,^{7a} (EOET)(TCNQ) (11) and κ -(ET)₂X,⁶ where HCTMM is hexacyanotrimethylenemethane. The S···S atomic contacts are less than the sum of the van der Waals radii for (a) BO and (c) ET compound.

Group B. In the BO system, there is no compound with $hv_{CT}^{solid} > 5 \times 10^3 \text{ cm}^{-1}$ in the redox region of $-0.02 \le \Delta E \le 0.34 \text{ V}$ [eqn. (2)]. On the other hand, two EOET complexes along the V-shaped line were obtained in this redox region (8, 15), and both exhibit an insulating character and thus are classified as a partial ionic CT complex with alternating stacks. This also indicates the reduced self-assembling ability of EOET molecules with respect to that of BO ones since the molecular self-aggregation would prefer segregated stacks rather than alternating ones. The insulating complexes 16, 20b, 20c, 21 and 22 located in the range of eqn. (1) ($-0.25 \le \Delta E \le 0.60 \text{ V}$) are also classified into Group B.

Fig. 5a shows the molecular structures in $(MeO)_2TCNQ$ complex **16** viewed on the molecules. Both component molecules are almost flat and form DDA alternating columns (Fig. 5b). Since an inversion center is present at the center of the acceptor molecule, DAD is the repeating unit. The interplanar spacings of DD and DA along the stack are appropriate for a CT solid (3.56 Å and 3.50–3.54 Å, respectively). The head-to-tail stacking in a DD dimer results in the absence of the CH···O hydrogen bond, also there are no tight atomic contacts between EOET and $(MeO)_2TCNQ$ molecules. The IR-active C=N stretching mode that appeared at 2213 cm⁻¹ is very close to that of neutral $(MeO)_2TCNQ^-$ (2198 and 2175 cm⁻¹), indicating a nearly neutral ionicity of **16**.

Single crystals of 1 : 1 (20b) and 1 : 2 (20c) BTDA-TCNQ complexes are obtained simultaneously by diffusion method and then separated under a microscope. However, attempts to obtain the single crystals of 3 : 2 complex (20a), which exhibits a high conductivity (23 S cm⁻¹ at RT) and is classified into Group A (see Table 1), are presently unsuccessful.

Typical DA alternating stacks are established in the 1 : 1BTDA-TCNQ complex (**20b**) (Fig. 6a). The orientation of EOET molecules is completely disordered and the donor plane is not parallel to the acceptor molecule but has a dihedral angle of 4.7°. The distance between two donor molecules along the stack is 6.95 Å.

As seen in Fig. 6b, a DA alternating column in the 1 : 2 BTDA-TCNQ complex (**20c**) is sandwiched by additional BTDA-TCNQ molecules. Similar to the 1 : 1 complex, the molecular planes of donor and acceptor in the same column are not parallel to each other but have a dihedral angle of 1.2° . The



Fig. 5 Crystal structure of $(EOET)_2[(MeO)_2TCNQ]$ (16) (a) projected perpendicular to the molecular planes and (b) along the molecular short axes.

interplanar spacings of DD and DA along the stack are 6.89 Å and 3.38–3.42 Å, respectively.

Since the $v_{\rm CN}$ mode at 2230 cm⁻¹ in BTDA-TCNQ⁰ redshifts to 2192 cm⁻¹ in the anion radical salt Li⁺(BTDA-TCNQ⁻), BTDA-TCNQ molecules in the 3 : 2 complex (**20a**) with $v_{\rm CN}$ = 2190–2192 cm⁻¹ are in a completely ionized state. Also the charges on the BTDA-TCNQ molecules in the 1 : 1 (**20b**, $v_{\rm CN}$ = 2220 cm⁻¹) and 1 : 2 (**20c**, $v_{\rm CN}$ = 2226 cm⁻¹) complexes are evaluated to 0.3 and 0.1 respectively, on the assumption of a linear relation between the $v_{\rm CN}$ mode and the charge on the BTDA-TCNQ molecules. Then the charges on EOET molecules are readily deduced to be *ca.* 0.7, 0.3 and 0.2 for the 3 : 2 (**20a**), 1 : 1 (**20b**) and 1 : 2 (**20c**) complexes, respectively.

Accordingly, the rather small degree of CT observed in 16, 20b and 20c gives the alternating stacks and thereby the display of both the insulating character and the $hv_{\rm CT}^{\rm solid}$ values along the V-shaped line.

Group C. For complexes **18b**, **19**, **23**, **24b** and **26**, the $hv_{\rm CT}$ ^{solid} values substantially exceed the values expected from the V-shaped line by 2–4.5 × 10³ cm⁻¹. The complexes **18b** and **19**, especially, are located far above the line by more than 4 × 10^3 cm⁻¹, which is evidently beyond the crystal field effect. Such a deviation is generally indicative of the different intermolecular interactions from the CT ones and/or the molecular packing depressing the Coulomb attractive energy.

The crystal structure of the *p*-iodanil (QI₄) complex (23) projected along the *b**-axis and along the molecular short axis of the EOET molecule are shown in Fig. 7a and 7b, respectively. Concave EOET and flat QI₄ molecules form a DDA alternating column along the (a + c) direction where a QI₄ molecule is encapsulated between two EOET molecules. Since both the center of the EOET dimer and the center of the QI₄ molecule are present at the inversion



Fig. 6 Crystal structures of (a) 1 : 1 BTDA-TCNQ complex (20b) projected along the *a*-axis and (b) 1 : 2 complex (20c) projected along the *b*-axis.

center, the repeating unit of the complex is DAD in a fashion similar to that in the $(MeO)_2TCNQ$ complex (16). The molecular plane of QI_4 is not parallel to that of the central $C_6S_6O_2$ moiety in EOET with a dihedral angle of 13.4° . The EOET molecules form the head-to-tail stacking in the dimer, and so no hydrogen bond is available for the self-aggregation of EOET molecules in 23.

The overlap patterns of DAD and those of DD in 23 viewed on the molecules are also depicted in Fig. 7c and 7d, respectively. The distance between the averaged EOET molecular planes is rather long (4.11 Å) although the overlap mode in the EOET dimer is distinctly close to a bond-over-ring type (Fig. 7d). For the overlap pattern of DAD (Fig. 7c), the distance between the center of the QI₄ molecule and the central tetrathioethylene in the EOET molecule is also significantly long (3.98 Å), and the quinone ring in the QI_4 molecule hardly overlaps with the EOET ones ($s1 = 0.41 \times 10^{-3}$, $s2 = 0.96 \times 10^{-3}$) 10^{-3} , see Fig. 7a). Naturally no short heteroatomic contact such as I···S (4.18–4.88 Å vs. vdW distance of 3.78 Å) or O···S (3.35–3.70 Å vs. vdW distance of 3.32 Å) is present between the EOET and QI_4 molecules. Thus complex 23 should be regarded as a clathrate-type compound rather than a conventional CT one. The IR-active $v_{C=O}$ mode that appeared at 1656 cm⁻ resembles closely that in neutral QI₄ ($v_{C=0} = 1660 \text{ cm}^{-1}$), and the conductivity measurement indicates an insulating character $(\sigma_{\rm RT} < 10^{-8} \text{ S cm}^{-1}).$

The observed large hv_{CT}^{N} values in this group are readily interpreted as described previously, *i.e.*, the reduced Coulomb



Fig. 7 Crystal structure of $(EOET)_2(QI_4)$ (23): (a) projected along the *b**-axis; (b) along the molecular short axis of EOET molecule; (c) overlap mode of DAD; (d) overlap mode of DD. *s*1 and *s*2 are the overlap integrals between EOET and QI₄ molecules. Inversion centers are denoted as small open circles.

attractive interactions between component molecules (C) due to the molecular packing which is unfavorable for CT interactions according to eqn. (3),

$$hv_{\rm CT}{}^{\rm N} = I_{\rm P} - E_{\rm A} - C \tag{3}$$

where I_p and E_A are the ionization potential of the donor molecule and the electron affinity of the acceptor molecule, respectively. This situation is very reminiscent of the BO complex of H₂TNBP, in which intermolecular OH···O hydrogen bonds between H₂TNBP and BO molecules contribute mainly to the formation of the complex compared to the CT interactions, resulting in a distinct crystal structure among the BO compounds.^{7a}

Based on their unexpectedly large hv_{CT}^{solid} values together with the insulating characters and IR spectra exhibiting a superposition of individual component molecules (see Table 1), other complexes classified into this group (18b, 19, 24b, 26) are also anticipated to have analogous structural features, although structural refinement is presently successful only for 23.

Group D. Complexes **27**, **28a**, **28b**, **29** and **30** locate along the right side of the V-shaped line, indicating a neutral ground state with alternating stacks. Single crystals, enough to refine the crystal structures, are obtained only for the complexes with C_{60} , although the convergences are insufficient, likely due to the static or dynamic orientational disorder of C_{60} molecules (*R* values are 0.132 for **28a** and 0.208 for **28b**). Two structurally distinct 1 : 1 : 1(benzene) complexes, **28a** (block) and **28b** (plate), were identified by structural refinements. No distinguishing differences between both complexes are realized in IR, UV–Vis and conductivity measurements. The IR-active $F_{1u}(4)$ mode at 1428 cm⁻¹ was unchanged on complex formation.

The crystal structures of **28a** and **28b** are analyzed with a restriction of the rigid model for all C_{60} molecules. Moreover,

four and two disordered orientations are presumed for C₆₀ molecules in **28a** and **28b** respectively, and the orientation of EOET molecules is completely disordered in both complexes. For complex **28a**, the crystallographic data are: monoclinic, space group C2/c, a = 16.512(3), b = 13.577(1), c = 20.843(3) Å, $\beta = 102.193(6)^\circ$, V = 4567(1) Å³, Z = 4, R = 0.138. Fig. 8a shows the molecular packing projected on to the *bc*-plane. The C₆₀ molecules form one-dimensional columns along the



Fig. 8 (a) Crystal structure of the monoclinic phase of (EOET)(C_{60})-(benzene) (**28a**) projected along the *a*-axis. (b) van der Waals atomic contacts between EOET and C_{60} molecules (dashed lines) where the C_{60} molecule is represented as a circle.

c-axis with the distance between the centers of the fullerene sphere equal to 10.42 Å. Each C_{60} molecule forms a DA pair with a concave EOET molecule and the shortest intermolecular C···S or C···O atomic contacts (3.49–3.59 Å) are comparable to the vdW distance of C···S (3.55 Å) as shown by dotted lines in Fig. 8b. For EOET molecules, the dihedral angle between the central C_2S_4 moiety and adjacent $C_2S_2X_2$ (X = O or S) moiety is 22.7°. Neighboring DA columns along the *b*-axis are arranged with oppositely oriented EOET molecules. The crystal structure is essentially analogous to that of (DBTTF)(C_{60})(benzene).³¹

For complex 28b, the crystallographic data are: triclinic, space group $P\bar{1}$, a = 10.155(1), b = 10.289(1), c = 11.189(2) Å, $\alpha = 78.390(7), \beta = 78.102(5), \gamma = 84.129(7)^{\circ}, V = 1118.3(2)$ Å³, Z = 1, R = 0.226. As shown in Fig. 9, the C₆₀ molecules form a two-dimensional network in the ab-plane with the distances between the centers of the fullerene sphere equal to 10.16 Å (||a|) and 10.29 Å (||b|). The formation of the C₆₀ twodimensional layer³² is particularly fascinating for molecular solids, since such a segregated layer would be unfavorable for the neutral CT complex composed of conventional molecules bearing no hetero atoms.^{22b,33} The vacancies between the C₆₀ layers contain planar EOET and benzene molecules, whose centers are present at (1/2,0,0) and (0,1/2,0), respectively. Along the [011] and [011] directions, the EOET and C₆₀ molecules are arranged as DA alternating stacks, in which the shortest intermolecular C…S or C…O atomic contacts (3.13–3.71 Å) are comparable to the vdW distances of C…S (3.55 Å) and C…O (3.20 Å). These alternating stacks give rise to the CT absorption band expected from the V-shaped line. The molecular packing is essentially similar to that of $(OMTTF)(C_{60})(benzene)$.^{32c}

Group E. Insulating complexes **1b** and **2** with 1 : 1 stoichiometry locate in the vicinity of the left side of the V-shaped line, as expected for a fully ionic ground state with alternating stacks. However, the UV–Vis–NIR spectrum of F₄TCNQ complex (**2**) in KBr pellet exhibits two distinct absorption bands characteristic of intermolecular transitions between each EOET⁺ and F₄TCNQ⁻ radicals (9.0 × 10³ cm⁻¹ for EOET⁺ and 6.7 × 10³ cm⁻¹ for F₄TCNQ⁻), indicating the formation of segregated columns composed of individual fully



Fig. 9 Crystal structure of triclinic phase of $(EOET)(C_{60})$ (benzene) (28b).



Fig. 10 (a) Temperature dependence of static susceptibility of polycrystalline (EOET)(F_4TCNQ) (2) in an applied magnetic field of 1 kOe. The magnetic fields are applied along the directions approximately parallel (H_{\parallel} , \bullet) and perpendicular (H_{\perp} , \bigcirc) to the needle axes of crystals. Inset is the enlargement for the low temperature range. (b) Magnetic field dependence of magnetization at 1.9 K. Inset is the enlargement for the low magnetic field range.

ionized component molecules. The intermolecular transition energy between EOET⁺ radicals is intermediate between those of BO⁺ (7–10 × 10³ cm⁻¹ for (BO)₂Br(H₂O)₃) and ET⁺ (6 × 10³ cm⁻¹ for (ET)Br(H₂O)).²⁰

The anisotropy of static susceptibility γ in 2 (polycrystalline needles) as a function of temperature is demonstrated in Fig. 10a. The magnetic field (0.1 T) was applied along the directions approximately parallel (\parallel) and perpendicular (\perp) to the needle axes of the crystals. Both χ_{\parallel} and χ_{\perp} follow the Curie-like law above ca. 10 K, and take a maximum at around 7 K. Below the temperature, χ_{\parallel} decreases rapidly toward zero, while a more gradual decrease of susceptibility was observed in χ_{\perp} . The anisotropic susceptibility below the transition temperature immediately rules out the occurrence of a finite spin-gap such as a spin-Peierls transition, which has been previously reported for the F4TCNQ complexes of HMTXF (X = S, Se).³⁴ As seen in Fig. 10b, a spin-flop transition characteristic of an antiferromagnetic spin structure is observed at ca. 3 kOe, which is comparable to ca. 5 kOe in $(TMTSF)_2MF_6$ (M = P, As) with a spin density wave (SDW) ground state³⁵ and *ca.* 3 kOe in κ -(ET)₂Cu[N(CN)₂]Cl with a canted antiferromagnetic ground state.³⁶ Considering that both F4TCNQ complexes of BO and ET exhibit an antiferromagnetic ordering below the Néel temperature $(T_N)^{37}$ and that the transition temperature in 2 (7 K) is intermediate between those of (BO)(F_4TCNQ) (5.4 K)^{37a} and (ET)-(F_4TCNQ) (14 K),^{37b} the magnetic ground state in **2** below 7 K is readily attributed to the antiferromagnetism. Then it appears that the easy axis is approximately along the needle axis of the crystal. The possible high electronic dimensionality of **2** with respect to those of (HMTXF)(F_4TCNQ) (X = S, Se)

may be responsible for the occurrence of the antiferromagnetic ordering rather than the spin–Peierls one.

3 Conclusion and summary

By using an EOET molecule which is a hybrid between BO and ET, 36 kinds of CT complex were prepared with conventional organic acceptor molecules and classified into five groups (A-E). Owing to the existence of the selfaggregation of EOET molecules, 17 kinds of highly conductive complex (Group A) are scattered in the extensive redox range $(-0.25 \leq \Delta E \leq 0.60 \text{ V})$ in a fashion similar to the corresponding BO ones. However, the formation of the complexes classified into Groups B (partially ionic insulator with alternating stacks, 7 complexes) and C (neutral clathrate with high $hv_{\rm CT}^{\rm solid}$, 5 complexes), both of which are rarely found in BO compounds, is strongly indicative of the reduced self-assembling ability of EOET molecules compared to BO ones. This reduction is adequate to rationalize the appearance of polymorphism and the MI transition, both of which have been realized largely for ET compounds rather than BO ones. On the other hand, Groups D and E contain five completely neutral and two completely ionic CT complexes, respectively. In conclusion, the EOET molecules substantially inherit the typical characteristics of the corresponding BO and ET and allow for a structurally and electronically wide variety of molecular complexes.

4 Experimental

Materials

All the donor and acceptor molecules including commercially available ones were purified by recrystallization and/or sublimation. Solid CT complexes were prepared either by direct mixing or by diffusion methods in appropriate solvents (CH₃CN, tetrahydrofuran or benzene).

Measurements

Optical measurements were carried out on KBr disks on a Perkin-Elmer 1000 Series FT-IR (resolution 4 cm^{-1}) for IR and near-IR regions (400–7800 cm⁻¹) and on a Shimadzu UV-3100 spectrometer for near-infrared, visible and ultraviolet (UV–Vis–NIR) regions (3800–42000 cm⁻¹). For single crystals, the temperature dependence of IR spectra was measured with the aid of a Nicolet 800 FT-IR (800–7800 cm⁻¹, 9–300 K).

CV measurements were performed in CH₃CN solution with 0.1 M (TBA)(BF₄) with a Yanaco Polarographic Analyzer P-1100. The working and counter electrodes were Pt, the reference electrode was SCE, and the scan rate was 20 mV s⁻¹.

DC conductivities were measured by a standard four- or two-probe technique by attaching gold wires (10 μ m diameter) to the samples with gold paint (Tokuriki Kagaku, 8560-1A).

A Quantum Design MPMS–XL SQUID magnetometer was used to collect the magnetization data down to 1.9 K.

X-Ray diffraction data were collected on imaging plate type or automatic four circle diffractometers (Mac Science DIP-2020K, Mac Science MXC^{κ}) with graphite monochromated Mo K α radiation at RT. Crystal structures were solved by direct methods (SIR92) and refined by full matrix least-squares method on *F* or *F*² (SHELXL-93).³⁸ The position of the hydrogen atoms of EOET was determined assuming sp³ configuration with a C–H distance of 1.0 Å. The refined and calculated atomic parameters are summarized as supplementary materials.¶

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